

P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY

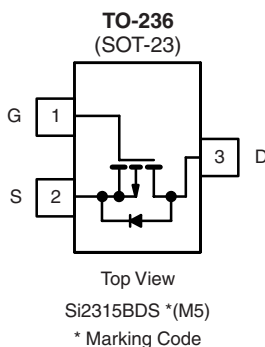
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.050 at $V_{GS} = - 4.5$ V	- 3.85
	0.065 at $V_{GS} = - 2.5$ V	- 3.4
	0.100 at $V_{GS} = - 1.8$ V	- 2.7

FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFETs: 1.8 V Rated



RoHS*
COMPLIANT



Ordering Information: Si2315BDS-T1
Si2315BDS-T1-E3 (Lead (Pb)-free)
Si2315BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

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Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	- 3.85	- 3.0	A
	T _A = 70 °C		- 3.0	- 2.45	
Pulsed Drain Current ^a		I _{DM}	- 12		
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.0	- 0.62	
Power Dissipation ^a	T _A = 25 °C	P _D	1.19	0.75	W
	T _A = 70 °C		0.76	0.48	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	85	105	°C/W
		130	166	
Maximum Junction-to-Foot (Drain)	R_{thJF}	60	75	

Notes:

a. Surface Mounted on FR4 board.

b. $t \leq 5$ s.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

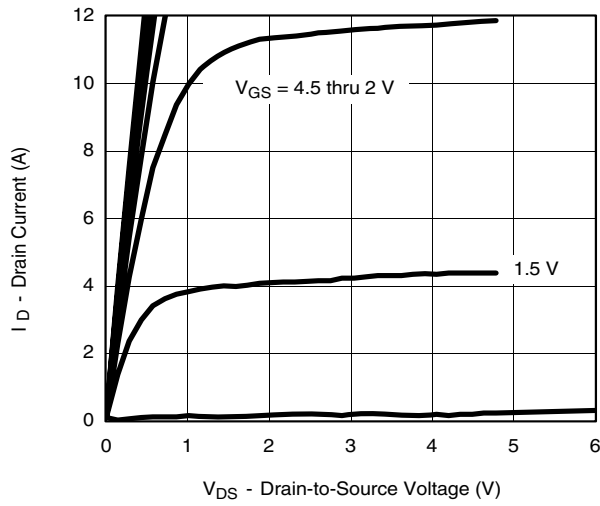
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = - 10 μA	- 12			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.45		- 0.90	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	- 6			A
		V _{DS} ≤ - 5 V, V _{GS} = - 2.5 V	- 3			
Drain-Source On Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.85 A		0.040	0.050	Ω
		V _{GS} = - 2.5 V, I _D = - 3.4 A		0.050	0.065	
		V _{GS} = - 1.8 V, I _D = - 2.7 A		0.071	0.100	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 5 V, I _D = - 3.85 A		7		S
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.6 A, V _{GS} = 0 V			- 1.2	V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = - 6 V, V _{GS} = - 4.5 V I _D ≅ - 3.85 A		8	15	nC
Gate-Source Charge	Q _{gs}			1.1		
Gate-Drain Charge	Q _{gd}			2.3		
Input Capacitance	C _{iss}	V _{DS} = - 6 V, V _{GS} = 0 V, f = 1 MHz		715		pF
Output Capacitance	C _{oss}			275		
Reverse Transfer Capacitance	C _{rss}			200		
Switching ^b						
Turn-On Time	t _{d(on)}	V _{DD} = - 6 V, R _L = 6 Ω I _D ≅ - 1.0 A, V _{GEN} = - 4.5 V R _G = 6 Ω		15	20	ns
	t _r			35	50	
Turn-Off Time	t _{d(off)}			50	70	
	t _f			50	75	

Notes:

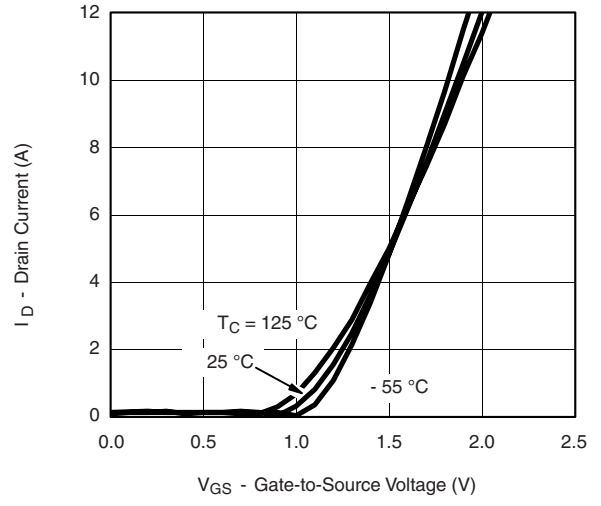
- a. For DESIGN AID ONLY, not subject to production testing.
b. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

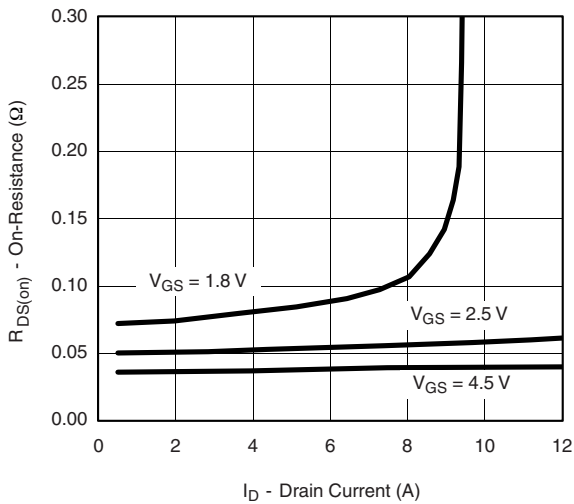
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



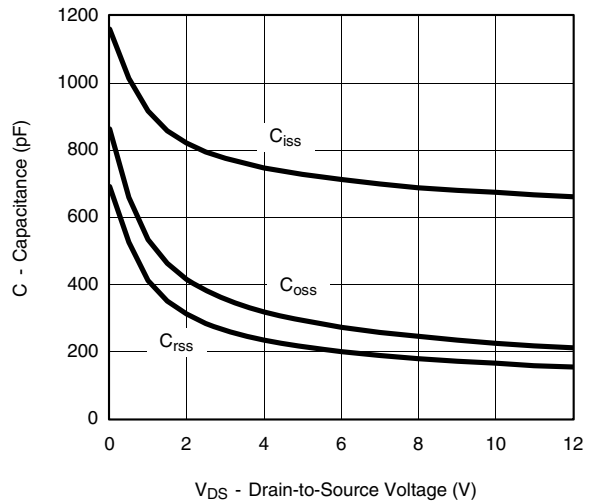
Output Characteristics



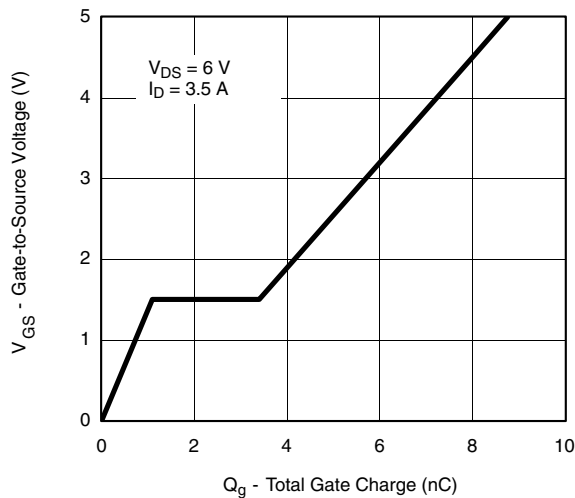
Transfer Characteristics



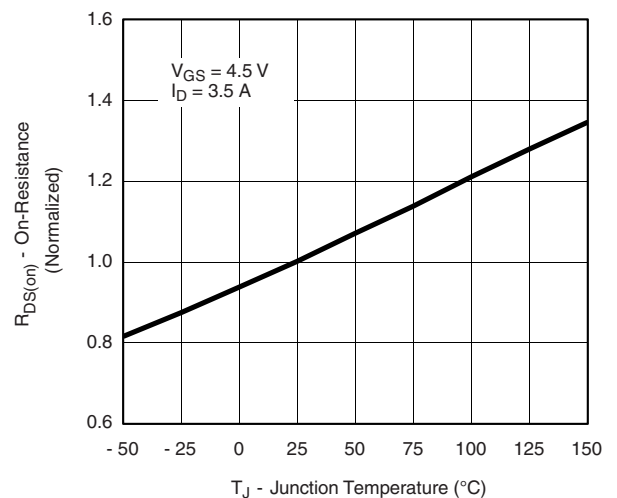
On-Resistance vs. Drain Current



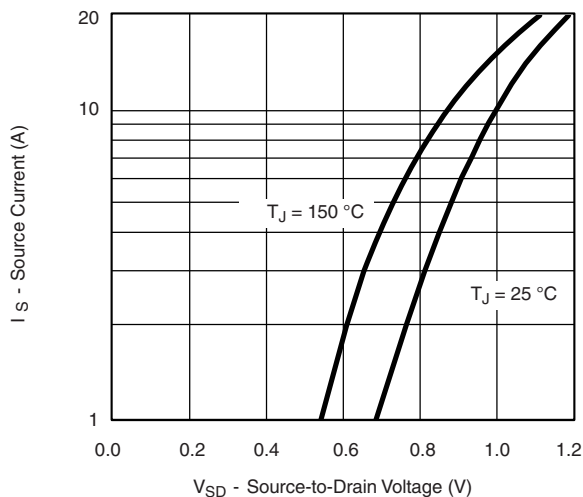
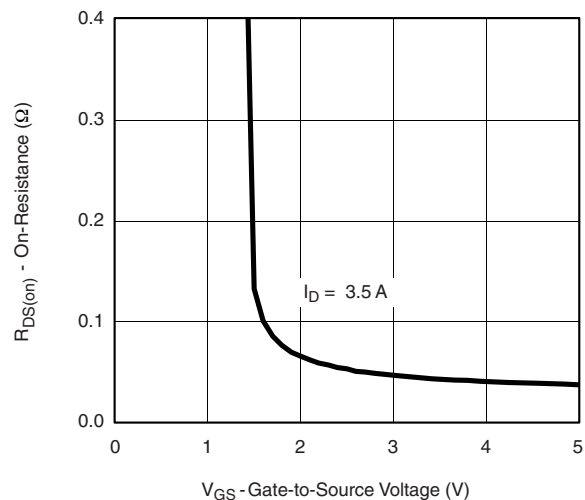
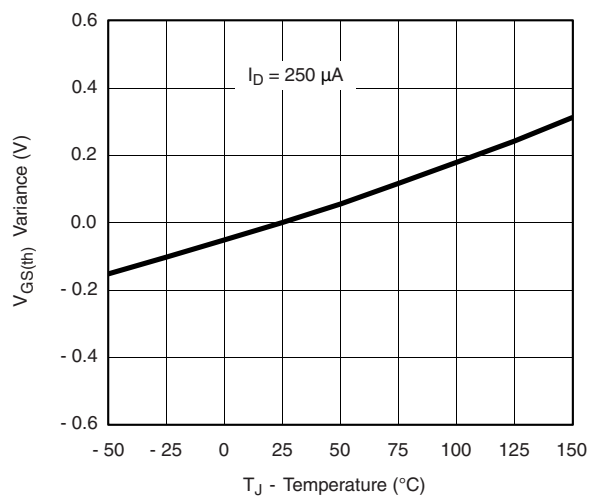
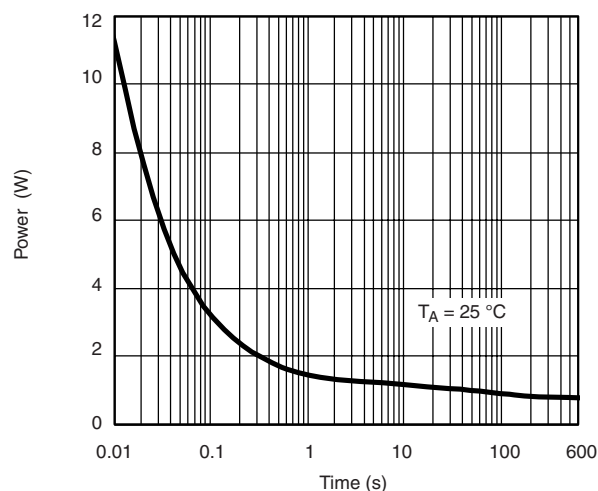
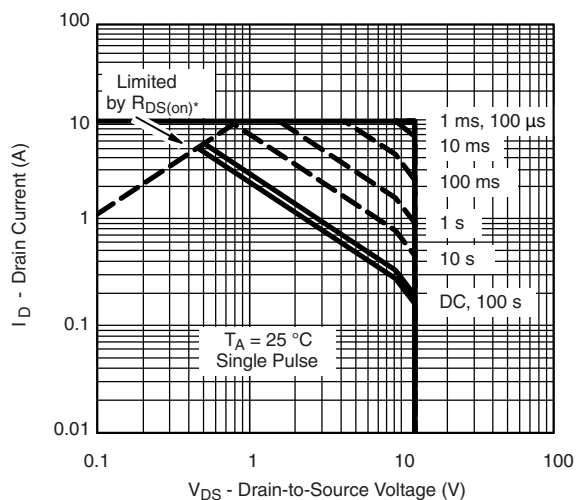
Capacitance



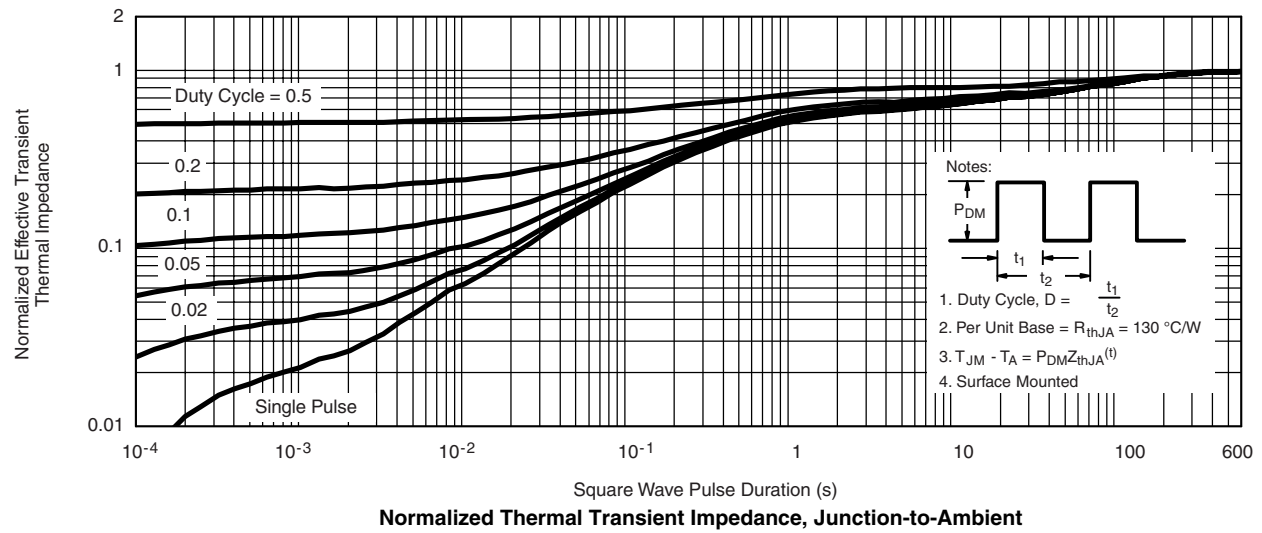
Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Safe Operating Area*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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